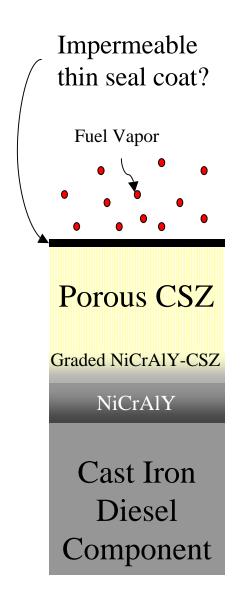
Morphology and High-temperature Stability of Amorphous Alumina Coatings Deposited on Si and CeO<sub>2</sub>-Stabilized ZrO<sub>2</sub> by MOCVD

> J. D. Meyer and W. Y. Lee Dept. of Materials Science & Engineering Stevens Institute of Technology

> > MRS 1998 Fall Meeting Boston, MA December 2, 1998

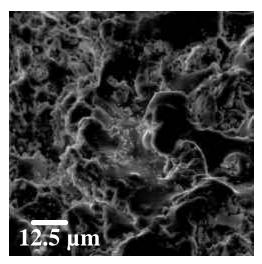
# **Rationale for Seal Coating**

- Thermal Barrier Coatings (TBCs) are being considered to improve diesel engine efficiency
  - CeO<sub>2</sub>-stabilized ZrO<sub>2</sub> (CSZ) prepared by air plasma spray (APS) provides thermal insulation of diesel components
  - APS-CSZ is made porous for strain tolerance and enhanced thermal insulation
- Unexpectedly, testing at Caterpillar revealed a decrease in engine efficiency when components were coated with a TBC
  - One possible reason may be the porosity of the TBC, which is suspected to "entrain" fuel from the combustion chamber prior to ignition [B. Beardsley, 1990]



# This Project Explores the Feasibility of Sealing the Surface of the TBC by Applying a Seal Coat

- Materials Criteria
  - Non-porous and impermeable
  - Good adhesion to CSZ
  - High thermal stability
  - No debit to CSZ strain tolerance
  - Resistance to erosion and wear
- Processing Criteria
  - Processing temperatures below
    500°C to avoid tempering of iron components
  - Conformal coating on complex, porous TBC surface



Surface morphology of APS-CSZ (as received)

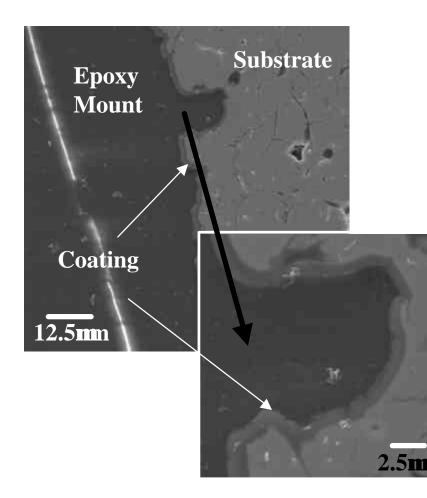
## Candidate Seal Coating Materials Were Screened Without Cast Iron Substrate

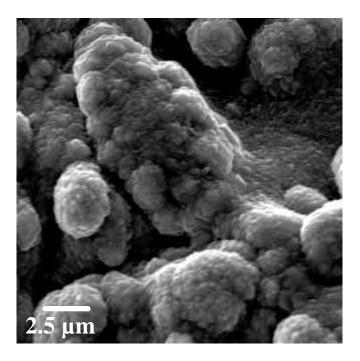
• "Free-standing" APS-CSZ coupons (1x1cm) were coated with:

| MATERIAL                                 | СТЕ            | MODULUS |
|--|----------------|---------|
|  | $(x10^{-6}/K)$ | (GPa)   |
| $\alpha$ -Al <sub>2</sub> O <sub>3</sub> | 8              | 380     |
| $3Al_2O_3 \cdot 2SiO_2$                  | 6              | 145     |
| $SiO_2$ (fused)                          | 0.5            | 70      |
| CSZ                                      | ~10            | ~200    |
| Si                                       | 3              | 163     |

- High-temperature chloride-based CVD processes were used:  $2AlCl_3 + 3CO_2 + 3H_2 \rightarrow Al_2O_3 + 6HCl + 3CO (1050^{\circ}C)$  $SiCl_4 + 2CO_2 + 2H_2 \rightarrow SiO_2 + 4HCl + 2CO (1050^{\circ}C)$
- Thermally cycled to 1150°C in air to assess seal coating/CSZ stability

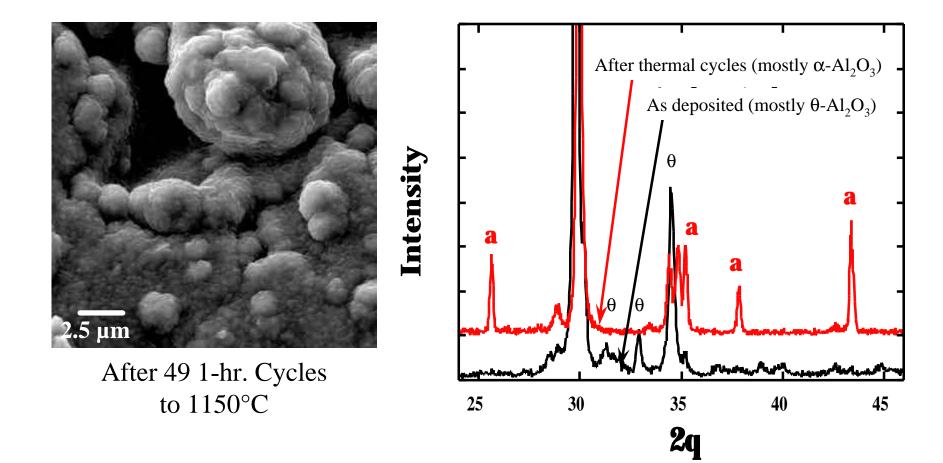
## Al<sub>2</sub>O<sub>3</sub> Seal Coating (from Chloride Process) Was Uniform and Conformal





As coated

## Al<sub>2</sub>O<sub>3</sub> Seal Coating (from Chloride Process) Was Stable upon Thermal Cycling



Initial Screening Results Suggest That Metastable  $Al_2O_3$  Seal Coating May Be Useful If It Can Be Prepared at  $T < 500^{\circ}C$ 

- $Al_2O_3$  was able to seal the porous CSZ surface
  - Although it transformed from  $\theta$  to  $\alpha$ -Al<sub>2</sub>O<sub>3</sub>

Free-standing CSZ without seal coating:



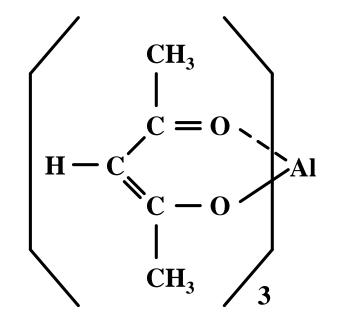
Free-standing CSZ coated and annealed:



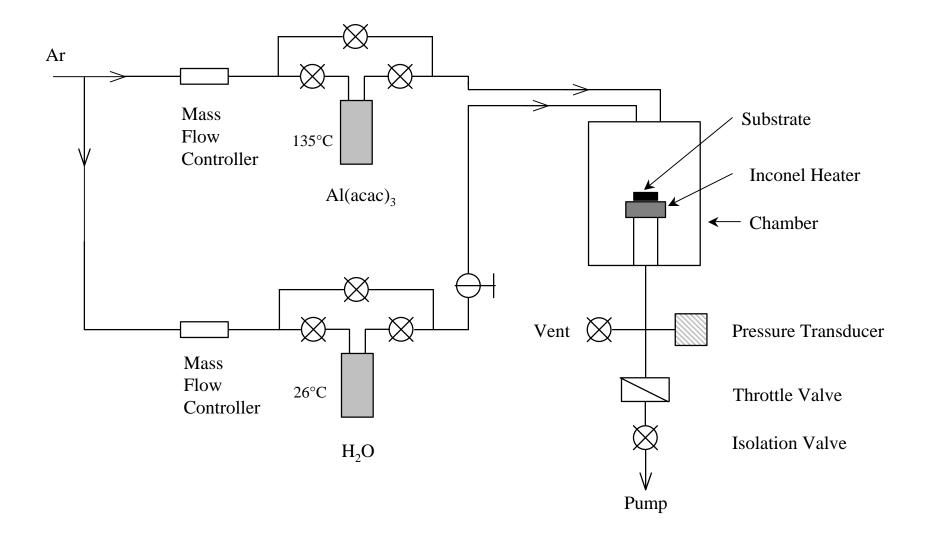
•  $3Al_2O_3 \cdot 2SiO_2$  and  $SiO_2$  spalled during thermal cycling, probably due to CTE mismatch with respect to CSZ

# $Al(acac)_3$ and $H_2O$ Were Selected to Prepare Low-temperature $Al_2O_3$ Seal Coating

- Major reasons:
  - Decomposes readily (well below 500°C)
  - Low toxicity and cost
  - Relatively moisture-insensitive
  - Stable compound at room temperature
  - Some carbon contamination observed
- Inclusion of water vapor appears to help eliminate carbon contamination [J.S. Kim, *et al.*, 1993]

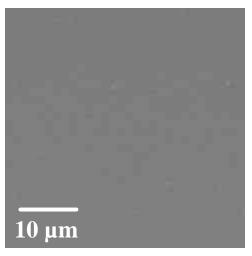


#### Cold-wall Al<sub>2</sub>O<sub>3</sub> MOCVD System Constructed

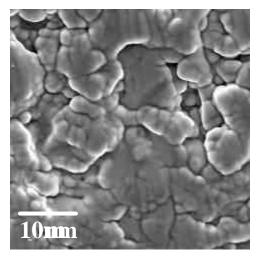


# MOCVD Al<sub>2</sub>O<sub>3</sub> Seal Coating Process Parameters Were Optimized

| Substrate temperature  | 505 ±5°C                              |
|--|---------------------------------------|
| Total pressure   | 1.33 kPa                              |
| Argon supply rate $(Al(acac)_3 / H_2O)$                        | 120 / 20 cm <sup>3</sup> /min         |
| Effective flow rate (Al(acac) <sub>3</sub> / H <sub>2</sub> O) | $0.43 / 0.67 \text{ cm}^3/\text{min}$ |
| Al(acac) <sub>3</sub> vaporization temperature                 | 130-135°C                             |



 $Al_2O_3$  on Si

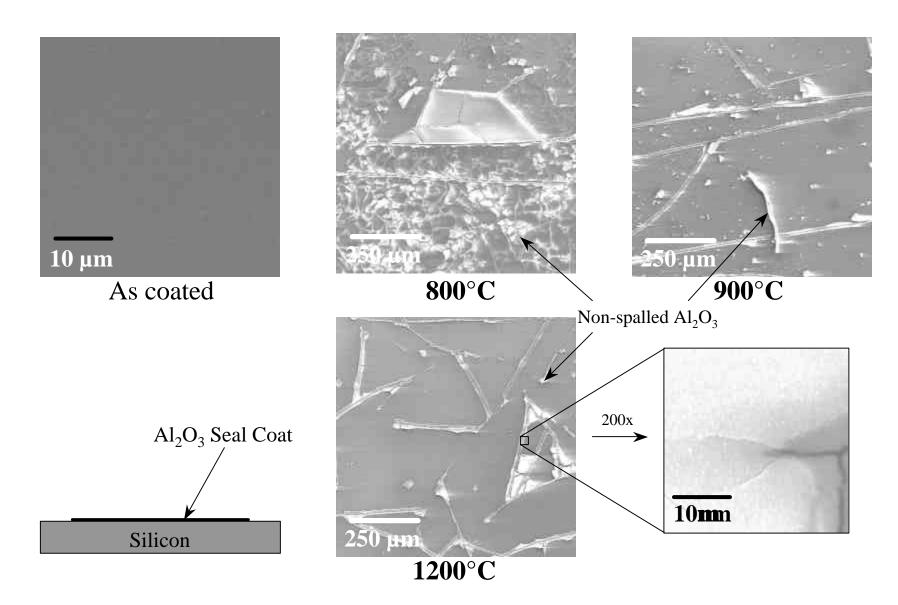


 $Al_2O_3$  on CSZ

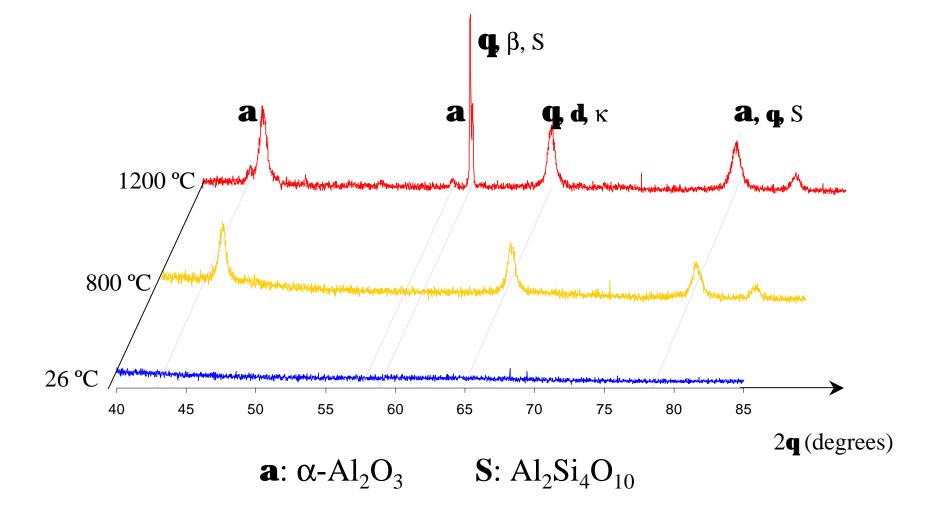
# Experimental Approach to Testing MOCVD $Al_2O_3$ Seal Coating

- Potential problems with MOCVD Al<sub>2</sub>O<sub>3</sub> coating:
  - Amorphous  $Al_2O_3$  with possible C and H impurities
  - Significant volume shrinkage expected upon crystallization (~ -9%)
- Substrate issues:
  - CSZ-coated iron flexure bar
  - Free-standing CSZ: CSZ without iron substrate
  - Silicon: ease of characterization, but large thermal mismatch
- Thermal exposure from 700°C to 1200°C in air for 20 hrs.

## MOCVD Al<sub>2</sub>O<sub>3</sub> on Silicon Spalled upon Annealing

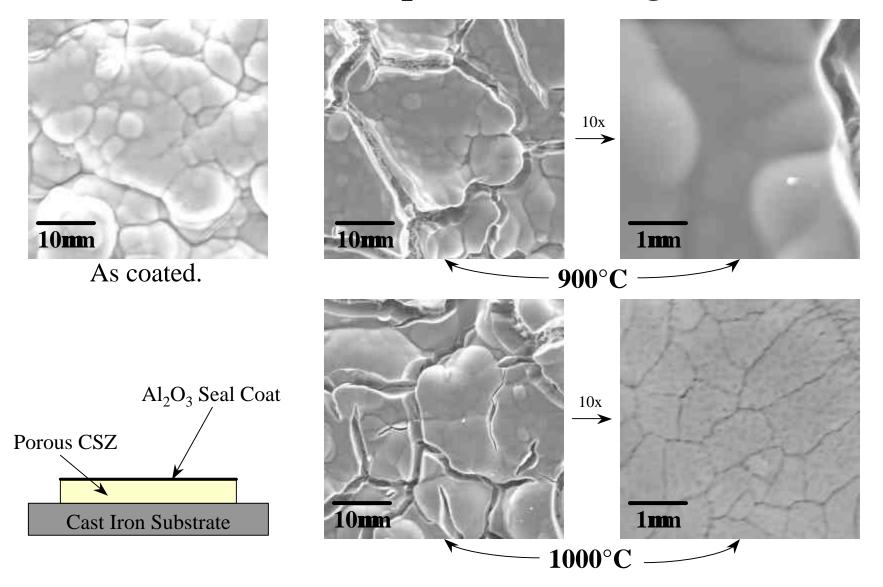


## Crystallization of MOCVD Al<sub>2</sub>O<sub>3</sub> Occurs Relatively Rapidly (20 Hours) at 700°C to 1200°C

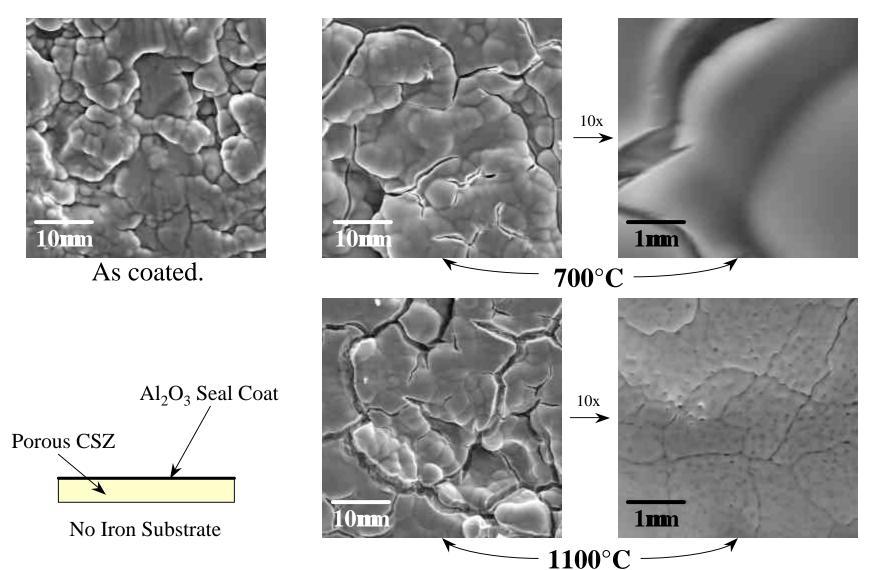


Not much  $Al_2O_3$  remained on the substrate for XRD analysis

## MOCVD Al<sub>2</sub>O<sub>3</sub> on Constrained CSZ/Iron Cracked Upon Annealing



## Metallic Substrate Had No Discernable Effect on Coating Behavior



# Annealing of MOCVD Al<sub>2</sub>O<sub>3</sub> Leads to Inadequate Adhesion and Sealing

- Considerable spallation on silicon
  - CTE mismatch
  - Volume shrinkage due to crystallization
- Adhered on CSZ, but coating cracked as crystallization occurred
  - Less CTE mismatch with CSZ than with Si
  - Better adhesion may be due to mechanical interlocking at CSZ/coating interface
  - Volume shrinkage still significant (~ 9%)

# Comparison of Chloride-based Al<sub>2</sub>O<sub>3</sub> vs. MOCVD Al<sub>2</sub>O<sub>3</sub>

|                               | Chloride-based<br>Al <sub>2</sub> O <sub>3</sub>  | MOCVD<br>Al <sub>2</sub> O <sub>3</sub>   |
|-------------------------------|---|---|
| As prepared:                  | Conformal, mostly<br>metastable (θ)   | Conformal, amorphous  |
| Thermally annealed:           | Retained adhesion & structural integrity  | Severe cracking, despite adhesion   |
| Crystallization:              | $\theta$ -Al <sub>2</sub> O <sub>3</sub> $\rightarrow \alpha$ -Al <sub>2</sub> O <sub>3</sub> | Amorphous $\rightarrow$<br>metastable, $\alpha$ -Al <sub>2</sub> O <sub>3</sub> |
|                               | $(\Delta V < -9\%)$   | $(\Delta V > -9\%)$   |
| Possible C & H<br>impurities: | Highly unlikely   | Possible, but<br>minimized  |
| Quality of sealing:           | "Sufficient"  | Insufficient  |

# **Conclusions**

- Chloride-based  $Al_2O_3$  coating deposited at 1050°C contained significant amounts of  $\theta$ -Al<sub>2</sub>O<sub>3</sub>.
- MOCVD Al<sub>2</sub>O<sub>3</sub> coating could be prepared at 500°C, but was entirely amorphous.
- Metastable  $Al_2O_3$  coating ( $\theta$ - $Al_2O_3$  minimum?) may be required to survive annealing and crystallization.
- Literature describes no MOCVD system in which a crystalline  $Al_2O_3$  coating can be deposited below 500°C.
- Alternative materials, along with a suitable coating process, still need to be explored.

## **Acknowledgments**

- Current research sponsored by Brad Beardsley at *Caterpillar, Inc.*
- The results from the chloride-based Al<sub>2</sub>O<sub>3</sub> coating work were obtained by W.Y. Lee at Oak Ridge National Laboratory under the sponsorship of Ray Johnson, *Heavy Vehicle Propulsion System Materials Program*, DOE Office of Transportation Technologies.